

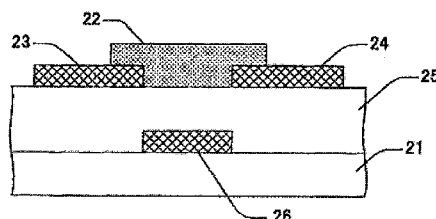


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(54) **Title:** P-TYPE OXIDE SEMICONDUCTOR, COMPOSITION FOR PRODUCING P-TYPE OXIDE SEMICONDUCTOR, METHOD FOR PRODUCING P-TYPE OXIDE SEMICONDUCTOR, SEMICONDUCTOR ELEMENT, DISPLAY ELEMENT, IMAGE DISPLAY DEVICE, AND SYSTEM

FIG. 3



(57) **Abstract:** A p-type oxide semiconductor, which contains: a metal oxide containing thallium (Tl), where the metal oxide has been hole doped.



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